IN THE CLAIMS

1. (currently amended): An intermediary semiconductor device, comprising:

a semiconductor substrate having a surface formed with a first recessed region;

a first dielectric material formed in the first recessed region;

a second recessed region formed within the first dielectric material, wherein the second recessed region has walls, a lower surface, and a first opening in proximity to the surface; and

a semiconductor layer formed overlying the first dielectric material having a second opening at least partially over the first opening, wherein ~~at least a portion of~~ the semiconductor layer is configured to at least partially convert to [[a]] an ~~semiconductor~~ oxide layer that covers the first opening while leaving a void in the second recessed region when the semiconductor substrate is subsequently exposed to an oxidizing environment to form the oxide layer.

Claims 2-4 (cancelled).

5. (previously presented): The semiconductor device of claim 1, wherein the semiconductor layer comprises polysilicon.

6. (original): The semiconductor device of claim 1, wherein the first dielectric material includes deposited silicon dioxide.

7. (previously presented): The semiconductor device of claim 1, further comprising a layer of material formed overlying the walls of the second recessed region.

8. (previously presented): The semiconductor device of claim 1, wherein the first dielectric material is recessed below a major surface of the semiconductor substrate.

9. (previously presented): The semiconductor device of claim 8, wherein the first dielectric material is recessed below the major surface a distance of about 0.5 microns.

10. (previously presented): The semiconductor device of claim 7, wherein the layer of material comprises polycrystalline silicon.

Claim 11 (cancelled).

Claims 12-25 (cancelled).

26. (currently amended): An intermediary of a semiconductor device, comprising:

a semiconductor substrate having a surface formed with a first recessed region;

a first dielectric material deposited in the first recessed region and formed with a second recessed region having a first opening and walls; and

a semiconductor cap layer formed overlying the first dielectric material and having a second opening at least partially over the first opening, wherein ~~at least a portion of~~ the semiconductor cap layer is configured to at least partially convert to ~~a semiconductor~~ an oxide that

covers the first opening while leaving a void in the second recessed region when the semiconductor substrate is subsequently exposed to an oxidizing environment.

27. (previously presented): The semiconductor device of claim 26, wherein the semiconductor cap layer comprises polysilicon.

Claim 28 (cancelled).

29. (previously presented): The semiconductor device of claim 26, wherein the first opening is wider than the second opening.

Claims 30-31 (cancelled).

32. (previously presented): The semiconductor device of claim 26, wherein the second recessed region is formed having a layer of material deposited on the walls.

33. (previously presented): The semiconductor device of claim 32, wherein the layer of material includes polycrystalline silicon.